

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S31	555	(257/793).CQLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/06/17 11:21
S30	402	(257/791).CQLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/06/17 11:21
S29	134	(438/457).CQLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/06/17 11:21
S28	16	S27 and (@ad<"20020225" @rlad<"20020225")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/17 11:20
S27	53	(stress\$2 near2 (balanc\$3 compensat\$3)) and (substrate wafer) near3 warp \$3 near3 prevent\$3	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/17 11:12
S24	187	S23 and (@ad<"20020225" @rlad<"20020225")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/17 09:55
S23	552	passivation adj (film layer) near4 (SiN silicon adj nitride) with (SiO silicon adj (dioxide oxide)) and IC	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/17 09:51
S22	870	S21 and (@ad<"20020225" @rlad<"20020225")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/17 09:50

S21	2345	passivation adj (film layer) near4 (SiN silicon adj nitride) with (SiO silicon adj (dioxide oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/17 09:37
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